

Phase Control Thyristors (Stud Version), 230 A



TO-93 (TO-209AB)

FEATURES

- Center amplifying gate
- International standard case TO-93 (TO-209AB)
- Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	230 A
V_{DRM}/V_{RRM}	1400 V, 1600 V
V_{TM}	1.55 V
I_{GT}	150 mA
T_J	-40 °C to +125 °C
Package	TO-93 (TO-209AB)
Circuit configuration	Single SCR

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		230	A
	T_C	85	°C
$I_{T(RMS)}$		360	A
I_{TSM}	50 Hz	5700	A
	60 Hz	5970	
I^2t	50 Hz	163	kA ² s
	60 Hz	149	
V_{DRM}/V_{RRM}		1400 to 1600	V
t_g	Typical	100	μs
T_J		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST230S	14	1400	1500	30
	16	1600	1700	



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		230	A
				85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 78 °C case temperature		360	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	5700	
		t = 8.3 ms	No voltage reapplied	5970	
		t = 10 ms	100 % V_{RRM} reapplied	4800	
		t = 8.3 ms	100 % V_{RRM} reapplied	5000	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	163	kA ² s
		t = 8.3 ms	No voltage reapplied	148	
		t = 10 ms	100 % V_{RRM} reapplied	115	
		t = 8.3 ms	100 % V_{RRM} reapplied	105	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		1630	kA ² √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.92	V
High level value of threshold voltage	$V_{T(TO)2}$	(I $> \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.98	
Low level value of on-state slope resistance	r_{t1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.88	mΩ
High level value of on-state slope resistance	r_{t2}	(I $> \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.81	
Maximum on-state voltage	V_{TM}	$I_{pk} = 720$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.55	V
Maximum holding current	I_H	$T_J = 25$ °C, anode supply 12 V resistive load		600	mA
Maximum (typical) latching current	I_L			1000 (300)	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}		1000	A/μs
Typical delay time	t_d	Gate current 1 A, $dI_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C		1.0	μs
Typical turn-off time	t_q	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $dI_F/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}		500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied		30	mA



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	180	-	mA
		$T_J = 25$ °C	90	150	
		$T_J = 125$ °C	40	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C	2.9	-	V
		$T_J = 25$ °C	1.8	3.0	
		$T_J = 125$ °C	1.2	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	V_{GD}		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.10	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-209AB)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



Fig. 1 - Current Ratings Characteristics



Fig. 2 - Current Ratings Characteristics



Fig. 3 - On-State Power Loss Characteristics



Fig. 4 - On-State Power Loss Characteristics

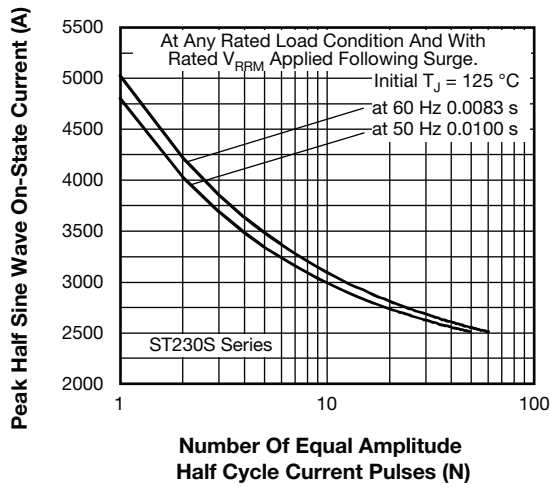


Fig. 5 - Maximum Non-Repetitive Surge Current

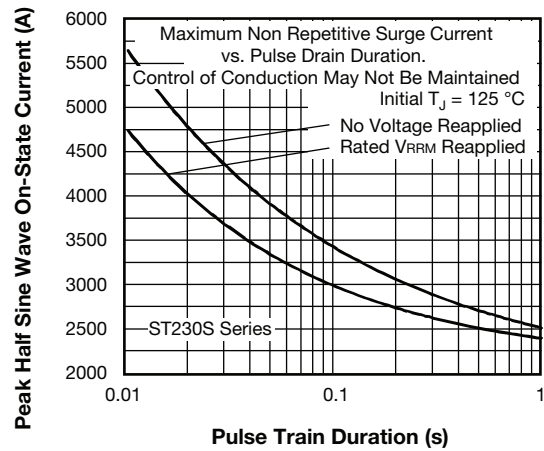


Fig. 6 - Maximum Non-Repetitive Surge Current

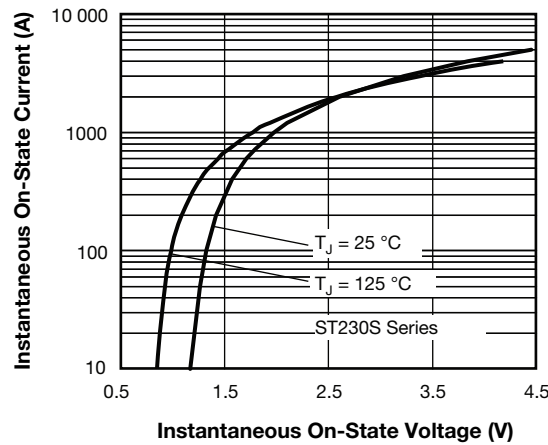


Fig. 7 - On-State Voltage Drop Characteristics

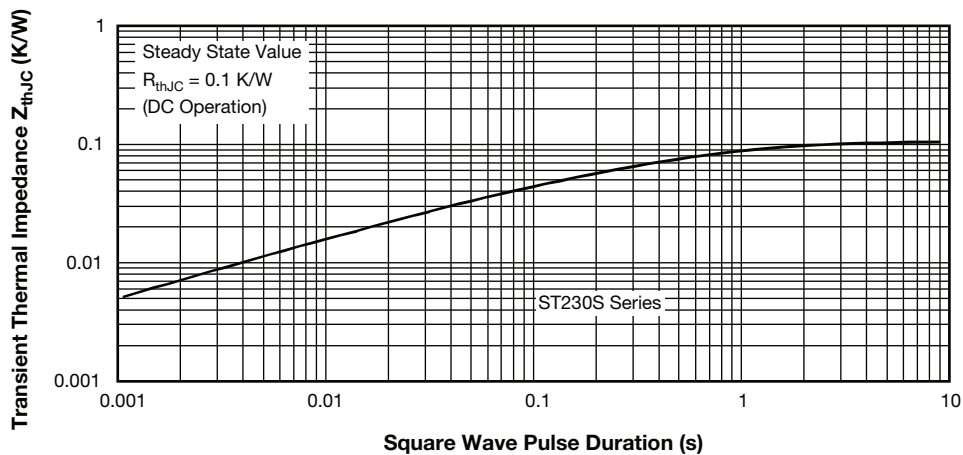


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	23	0	S	16	P	0	PbF
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 0 = converter grade
- 5** - S = compression bonding stud
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** - P = stud base 3/4"-16UNF2A threads
- 8** - 0 = eyelet terminals (gate and auxiliary cathode leads)
1 = fast-on terminals (gate and auxiliary cathode leads)
- 9** - None = standard production
- PbF = lead (Pb)-free

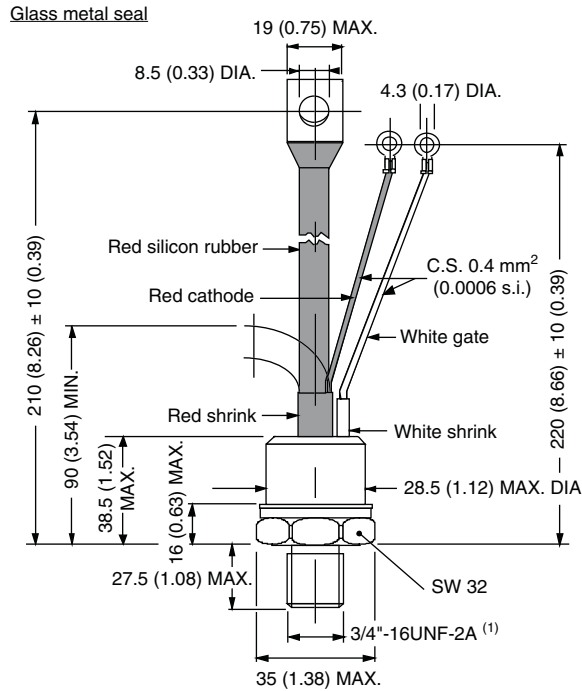
Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95082



TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)



Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



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